

IN THE CLAIMS

Claims 1-7 and 15-122 have previously been cancelled without prejudice as being drawn to non-elected inventions.

Claims 9 and 13 have also previously been canceled without prejudice.

Please amend claim 8.

Please enter the pending claims as follows:

1.- 7. (Cancelled)

8. (Currently Amended) A gate electrode, comprising:
a gate layer disposed over a substrate;
thin first spacers disposed adjacent to opposite sides of said gate layer;
thick second spacers disposed adjacent to said thin first spacers, said thin first spacers and said thick second spacers having vertical sidewalls that are parallel to each other along their entire height wherein said gate layer, said thin first spacers, and said thick second spacers have approximately the same height; and
a conductive layer disposed over said gate layer, said conductive layer extending laterally over said thin first spacers but not over sidewalls of said gate layer and not over said thick second spacers.

9. (Cancelled)

10. (Previously Presented) The gate electrode of claim 8, wherein said gate layer comprises polysilicon.

11. (Previously Presented) The gate electrode of claim 10, wherein said conductive layer comprises polycide.

12. (Previously Presented) The gate electrode of claim 8, wherein said thin first spacers comprise oxide.

13. (Cancelled).

14. (Previously presented) The gate electrode of claim 11, wherein said polycide comprises titanium salicide ($TiSi_2$).

15. – 122. (Cancelled)

123. (Previously Presented) The gate electrode of claim 8, wherein said thick second spacers comprise nitride.

124. (Previously Presented) The gate electrode of claim 8, wherein the thin first spacers are at least as high as the thick second spacers.

125. (Previously Presented) The gate electrode of claim 8, wherein the thick second spacers are at least twice as thick as the thin first spacers.

126. (Previously Presented) The gate electrode of claim 125, wherein the thick second spacers are between 300 and 2000 Å thick.

126. (Previously Presented) The gate electrode of claim 126, wherein the thick second spacers are at least 800 Å thick.

128. (Previously Presented) The gate electrode of claim 125, wherein the thick second spacers are at least 800/100 times as thick as the thin first spacers.